

HM30P55-VB Datasheet

P-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS}	-60	V
$R_{DS(on)} V_{GS} = 10\text{ V}$	19	$m\Omega$
$R_{DS(on)} V_{GS} = 4.5\text{ V}$	26	$m\Omega$
I_D	-50	A
Configuration	Single	

FEATURES

- Trench Power MOSFET
- 100 % UIS Tested

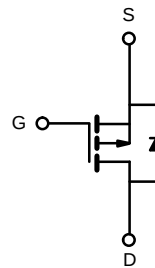
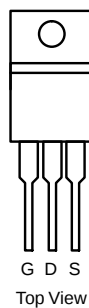
APPLICATIONS

- Load Switch



RoHS
COMPLIANT
HALOGEN
FREE

TO-220AB



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	- 60	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150\text{ }^\circ\text{C}$)	$T_C = 25\text{ }^\circ\text{C}$	I_D	- 50	A
	$T_C = 70\text{ }^\circ\text{C}$		- 46	
	$T_A = 25\text{ }^\circ\text{C}$		-39	
	$T_A = 70\text{ }^\circ\text{C}$		-34	
Pulsed Drain Current		I_{DM}	- 200	mJ
Avalanche Current Pulse		I_{AS}	- 45	
Single Pulse Avalanche Energy		E_{AS}	101	mJ
Continuous Source-Drain Diode Current	$T_C = 25\text{ }^\circ\text{C}$	I_S	69 ^a	
	$T_A = 25\text{ }^\circ\text{C}$		20 ^b	W
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	104.2 ^a	
	$T_C = 70\text{ }^\circ\text{C}$		66.7 ^a	
	$T_A = 25\text{ }^\circ\text{C}$		3.1 ^b	
	$T_A = 70\text{ }^\circ\text{C}$		2 ^b	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	Steady State	R_{thJA}	33	40	$^\circ\text{C/W}$
Maximum Junction-to-Case	Steady State	R_{thJC}	0.98	1.2	

Notes:

a. Based on $T_C = 25\text{ }^\circ\text{C}$.

b. Surface mounted on 1" x 1" FR4 board.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 60			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		68		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.2		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1		- 3	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 60 V, V _{GS} = 0 V			- 1	μA
		V _{DS} = - 60 V, V _{GS} = 0 V, T _J = 55 °C			- 10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 120			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 30 A		19		mΩ
		V _{GS} = - 4.5 V, I _D = - 20 A		26		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 50 A	20			S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		3700		pF
Output Capacitance	C _{oss}			390		
Reverse Transfer Capacitance	C _{rss}			290		
Total Gate Charge	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 55 A		76	115	nC
		V _{DS} = - 30 V, V _{GS} = - 4.5 V, I _D = - 55 A		38	60	
Gate-Source Charge	Q _{gs}			16		
Gate-Drain Charge	Q _{gd}			19		
Gate Resistance	R _g	f = 1 MHz		5.2		Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = - 2 V, R _L = 2 Ω I _D ≡ - 10 A, V _{GEN} = - 10 V, R _g = 1 Ω		10	15	ns
Rise Time	t _r			7	15	
Turn-Off Delay Time	t _{d(off)}			70	110	
Fall Time	t _f			40	60	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 69	A
Pulse Diode Forward Current ^a	I _{SM}				- 150	
Body Diode Voltage	V _{SD}	I _S = - 30 A		- 1	- 1.5	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 50 A, di/dt = 100 A/μs, T _J = 25 °C		45	68	ns
Body Diode Reverse Recovery Charge	Q _{rr}			59	120	nC
Reverse Recovery Fall Time	t _a			29		ns
Reverse Recovery Rise Time	t _b			16		

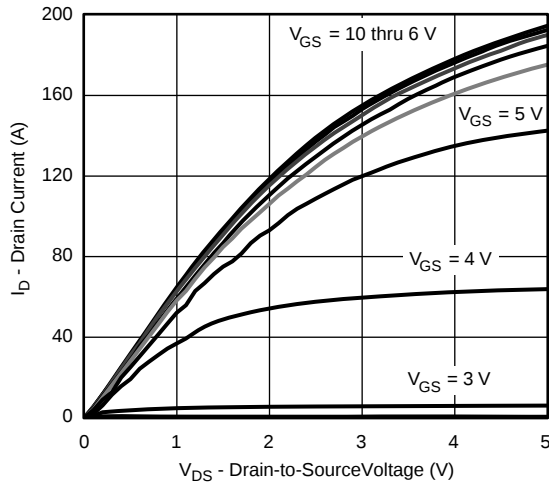
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

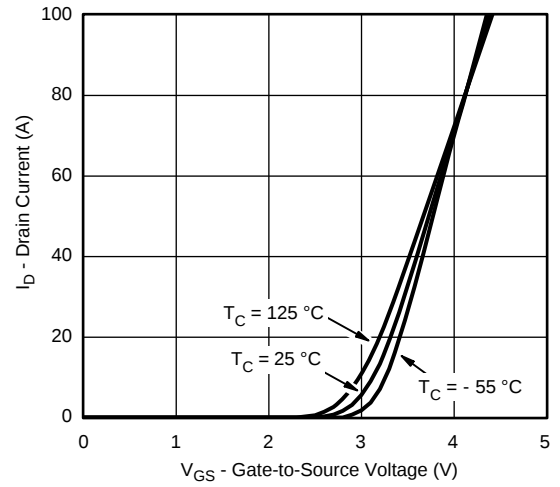
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

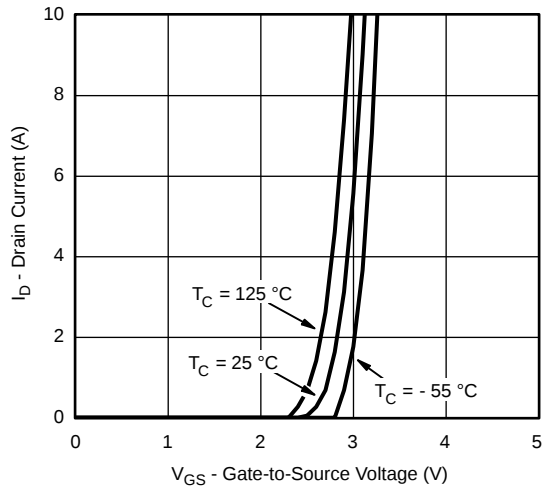
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics



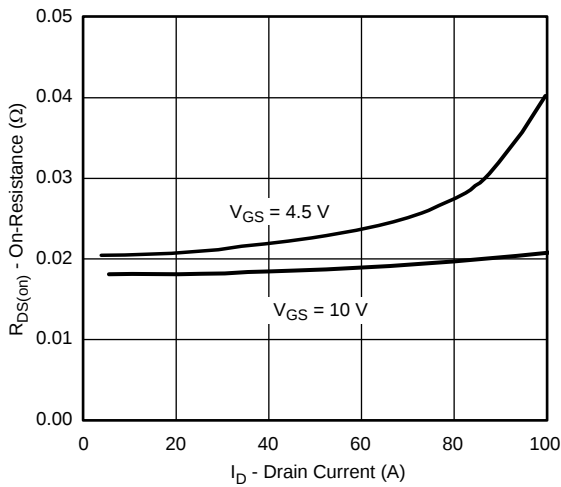
Transfer Characteristics



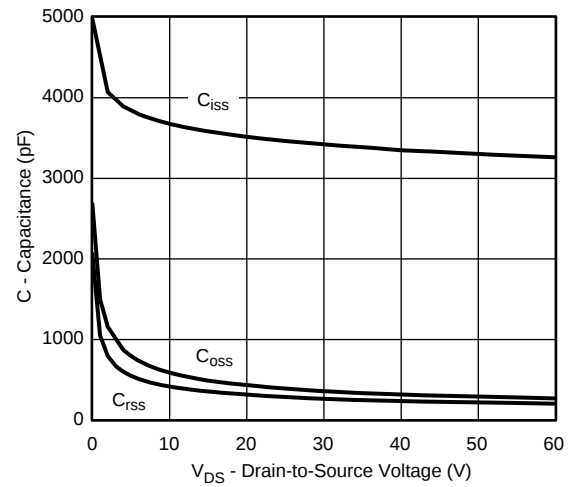
Transfer Characteristics



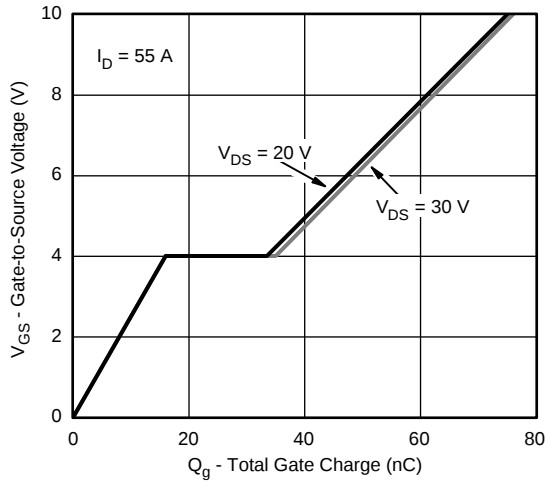
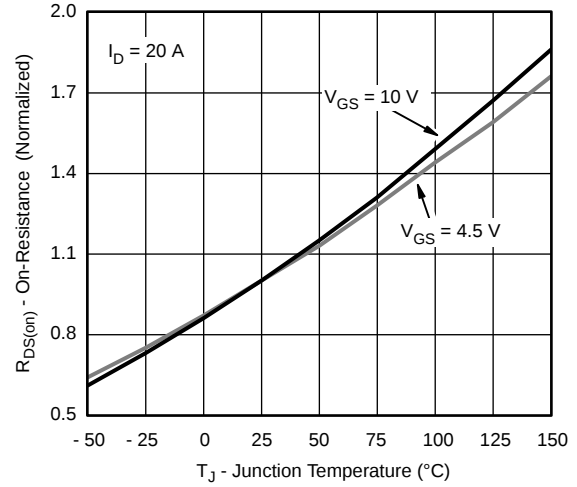
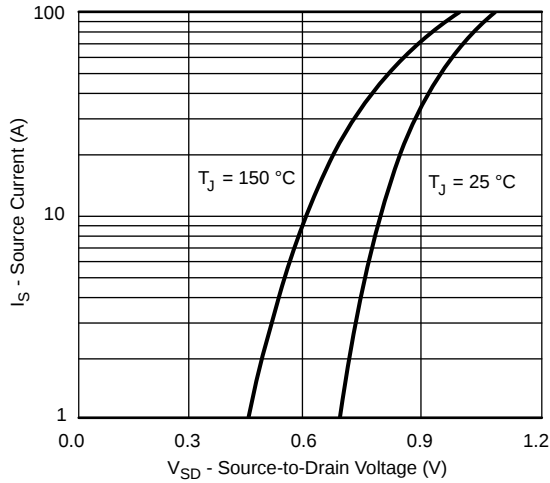
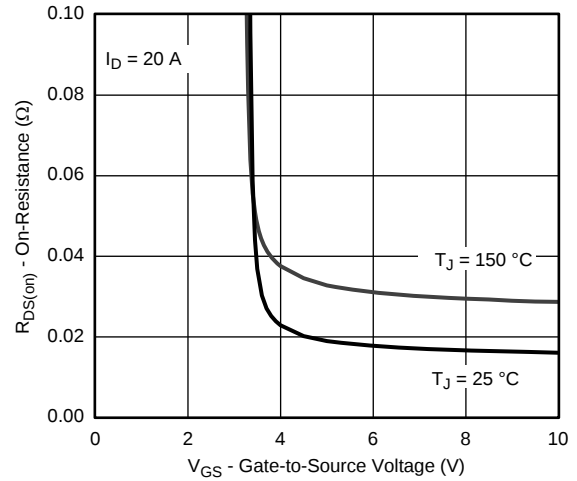
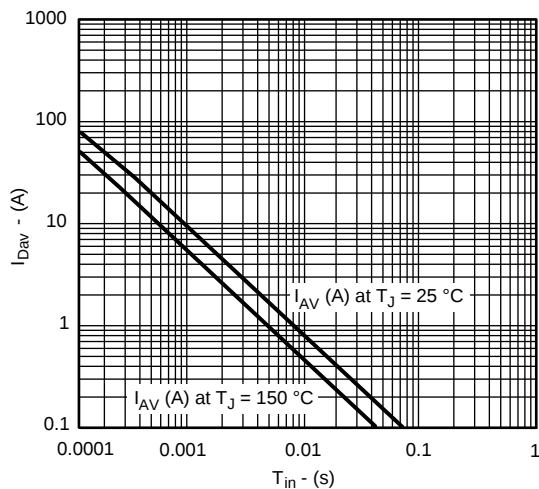
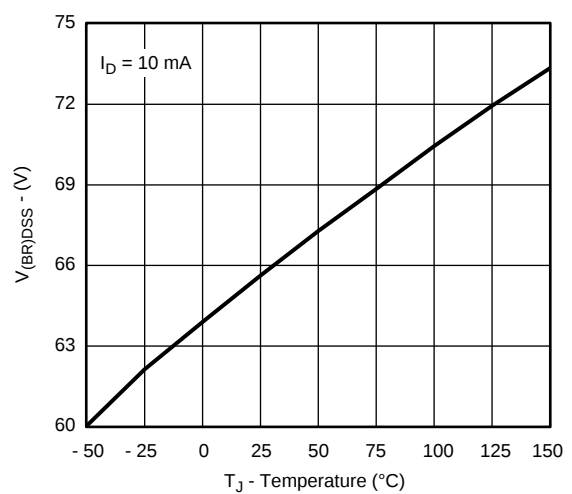
Transconductance



On-Resistance vs. Drain Current



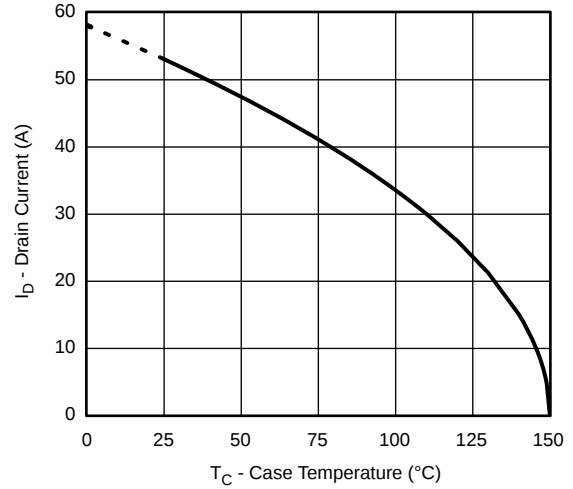
Capacitance

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Gate Charge

On-Resistance vs. Gate-to-Source Voltage

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Single Pulse Avalanche Current Capability vs. Time

Drain-Source Breakdown Voltage vs. Junction Temperature

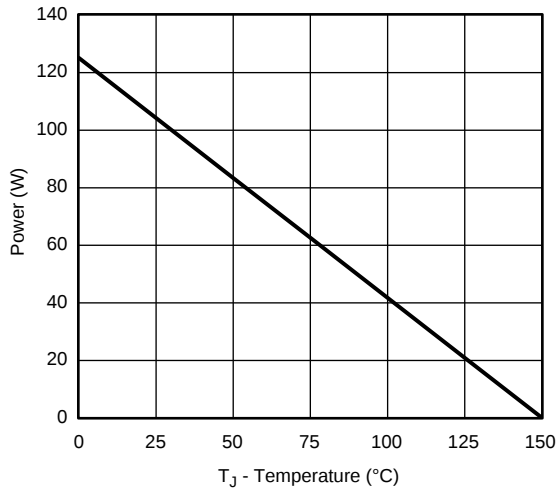
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



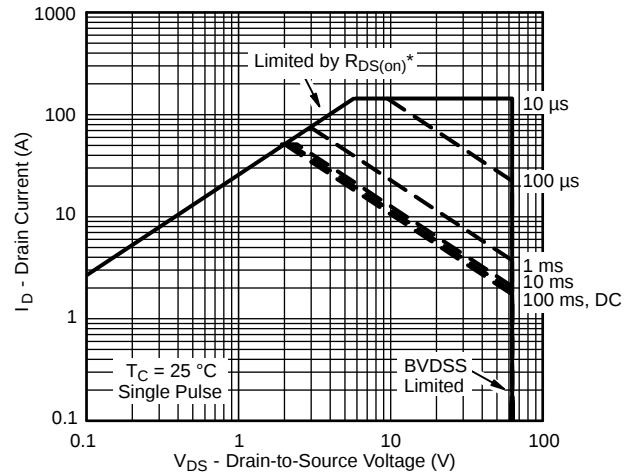
Threshold Voltage



Max. Drain Current vs. Case Temperature

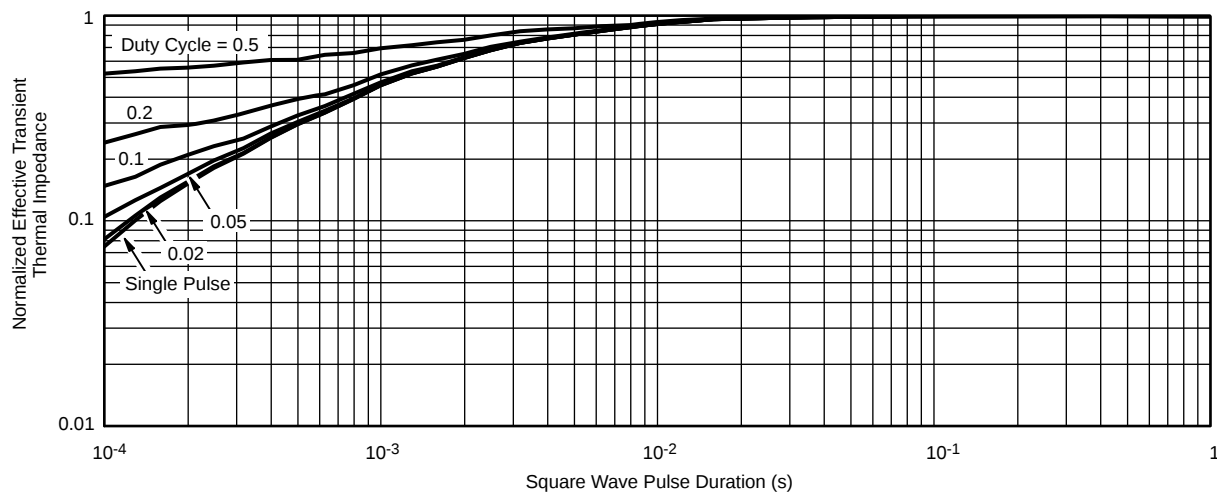


Power Derating, Junction-to-Case



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Case

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: X12-0208-Rev. N, 08-Oct-12				
DWG: 5471				

Notes

* M = 1.32 mm to 1.62 mm (dimension including protrusion)
 Heatsink hole for HVM

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